

# Device Modeling Report

COMPONENTS:  
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD  
PART NUMBER: RURG5060  
MANUFACTURER: INTERSIL  
REMARK: TC=150C

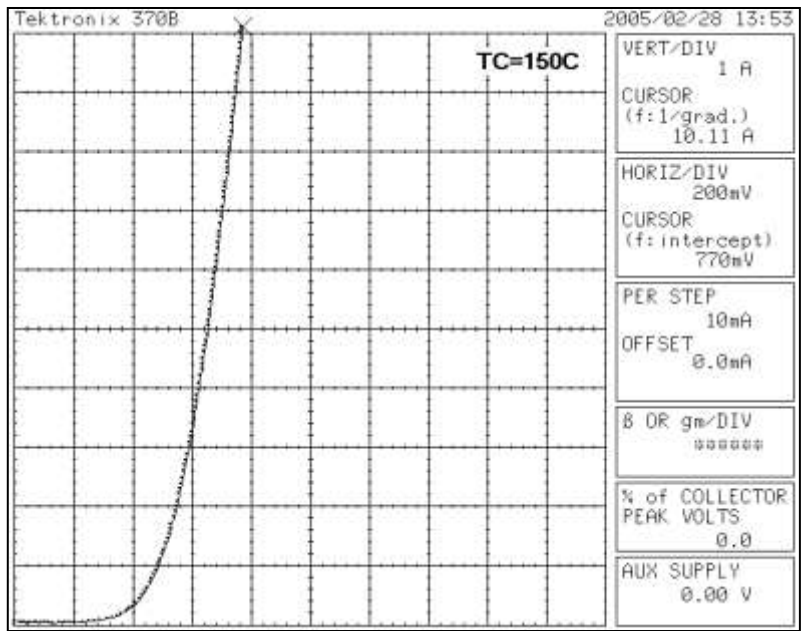


**Bee Technologies Inc.**

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

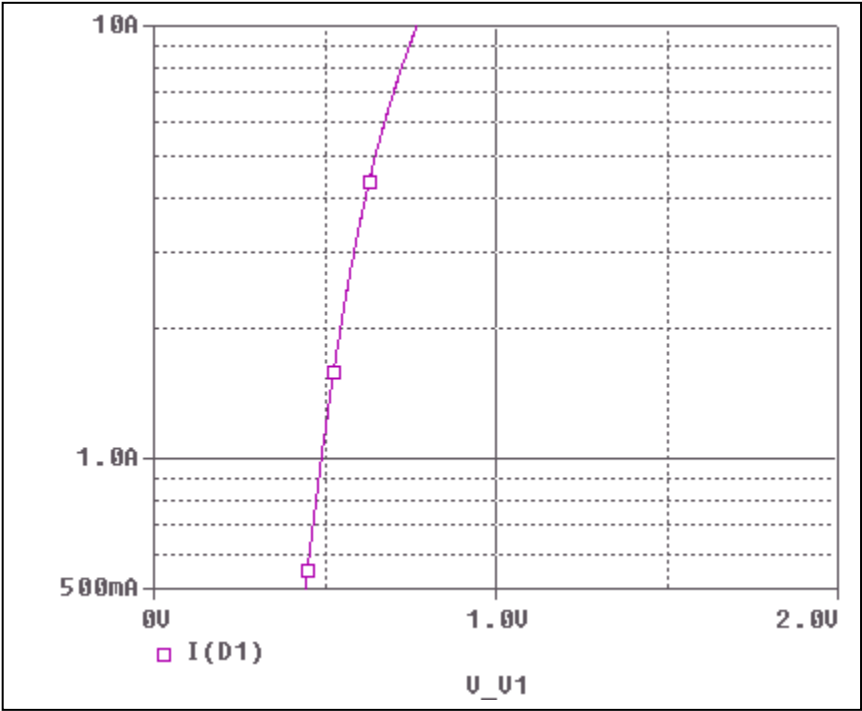
# Forward Current Characteristic

# Reference

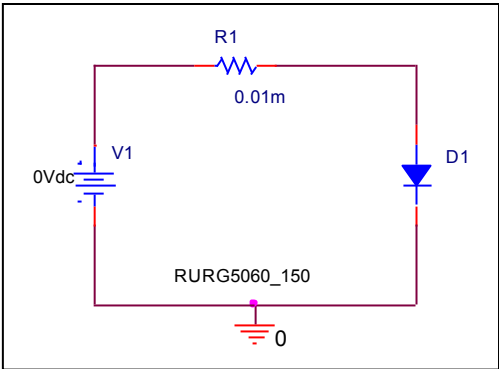


# Forward Current Characteristic

## Circuit Simulation Result

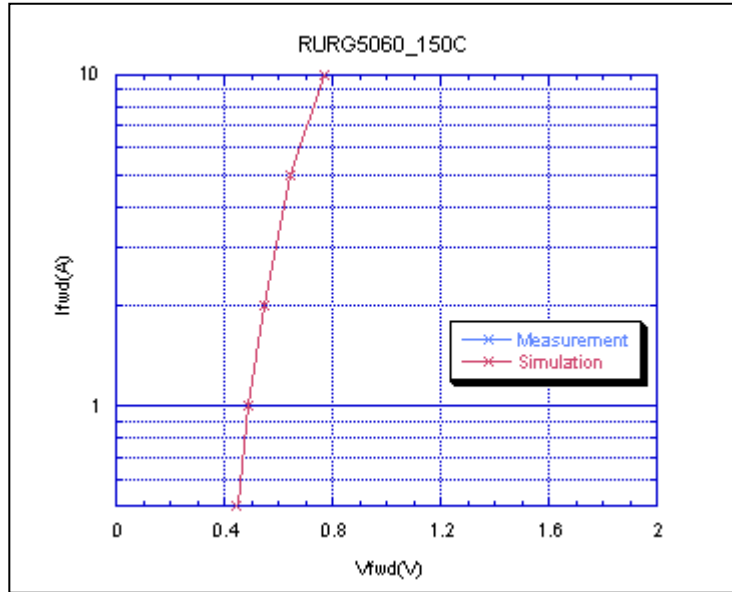


## Evaluation Circuit



# Comparison Graph

## Circuit Simulation Result

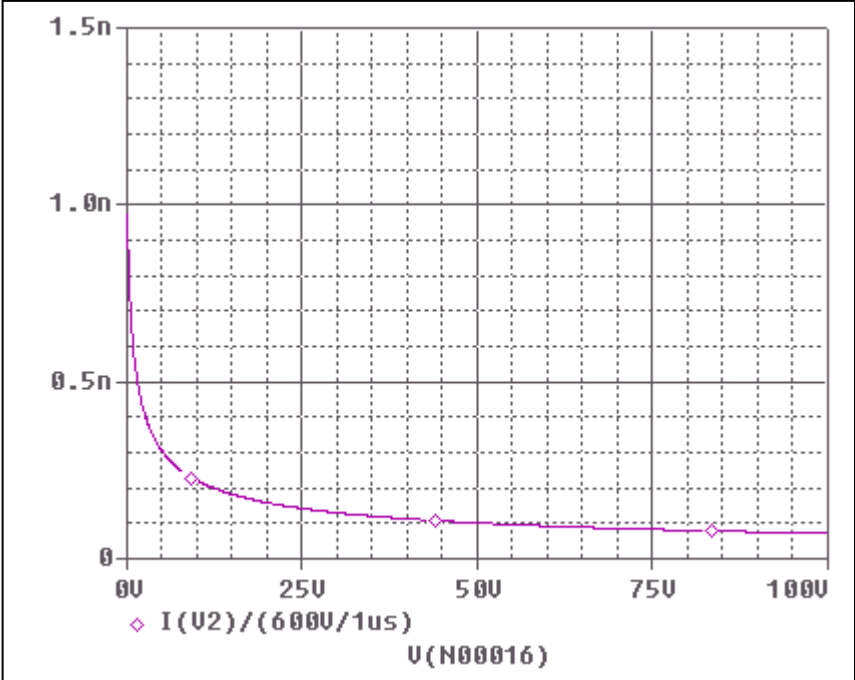


## Simulation Result

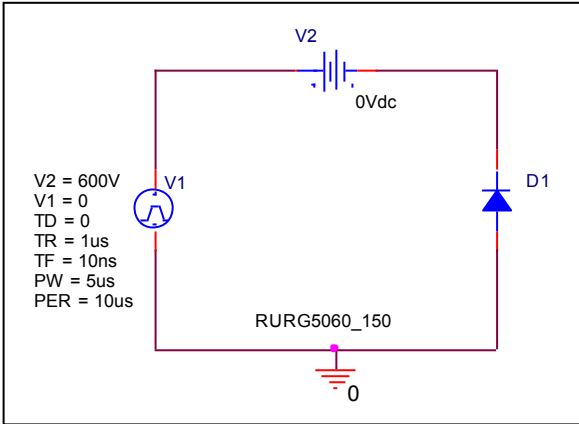
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.5	0.444	0.443	0.23
1	0.488	0.489	-0.20
2	0.548	0.547	0.18
5	0.646	0.647	-0.15
10	0.770	0.771	-0.13

# Capacitance Characteristic

## Circuit Simulation Result

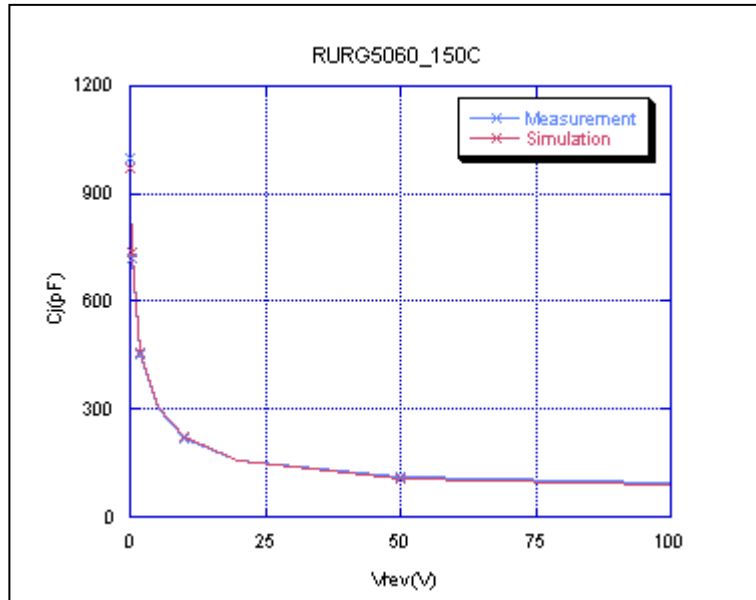


## Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

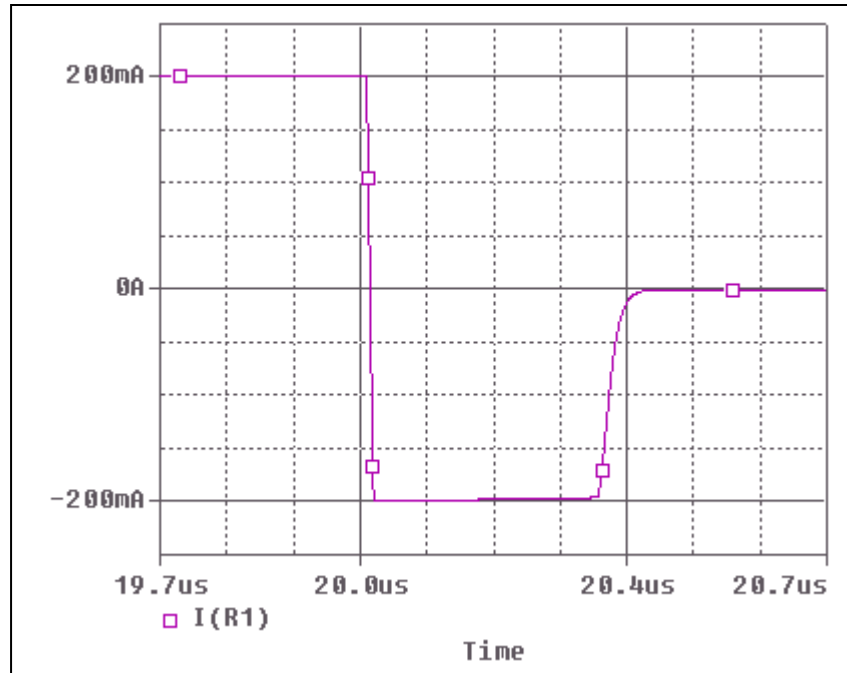


### Simulation Result

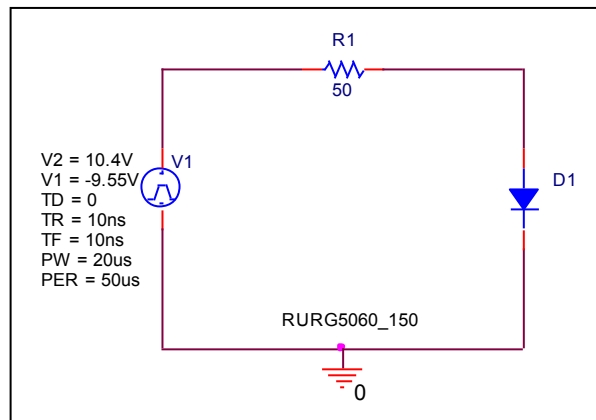
$V_{rev}$ (V)	$C_j$ (pF) Measurement	$C_j$ (pF) Simulation	%Error
0	1024.500	1024.500	0.00
0.1	1000.300	972.127	2.82
0.2	873.719	891.484	-2.03
0.5	716.756	734.007	-2.41
1	591.286	593.228	-0.33
2	450.101	456.899	-1.51
5	299.470	306.362	-2.30
10	220.151	221.603	-0.66
20	155.711	158.498	-1.79
50	110.788	107.342	3.11
100	90.100	85.854	4.71

# Reverse Recovery Characteristic

## Circuit Simulation Result



## Evaluation Circuit



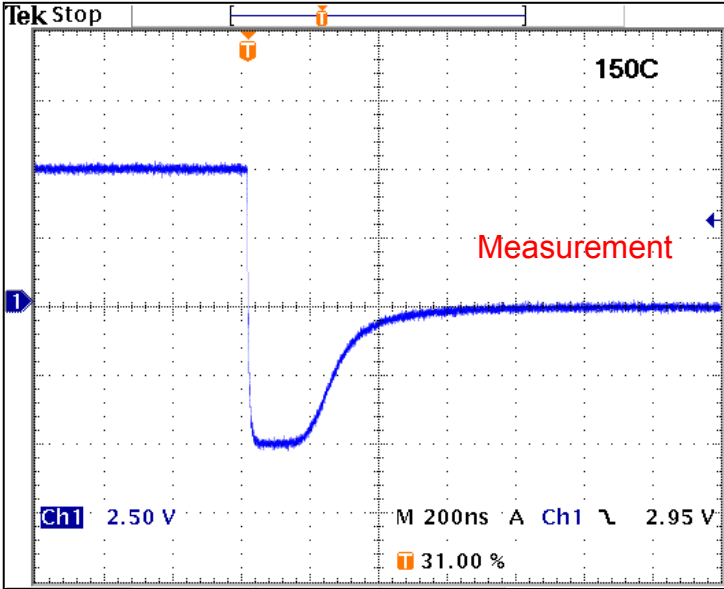
## Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	380.0	ns	379.0	ns	0.263

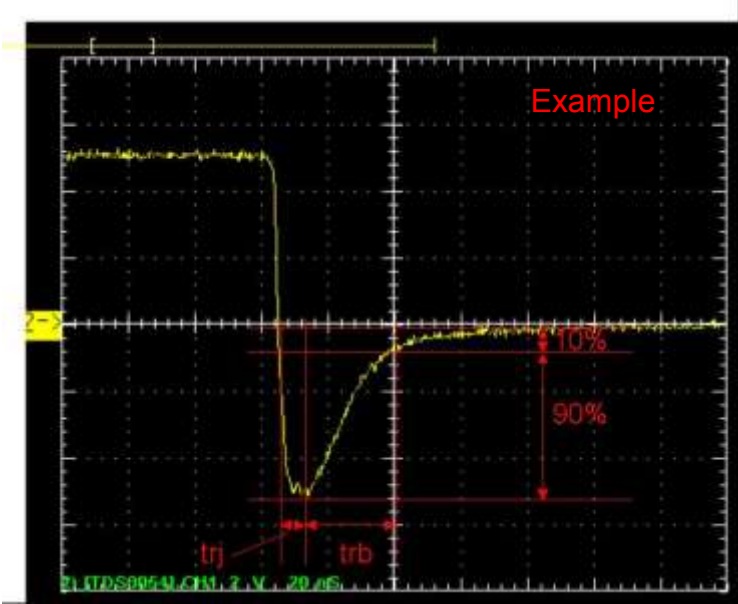


# Reverse Recovery Characteristic

# Reference



Trj =132 (ns)  
Trb= 248 (ns)  
Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb